TOSHIBA TRANSISTOR

2SC3298B

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

T-33-09

POWER AMPLIFIER APPLICATIONS.

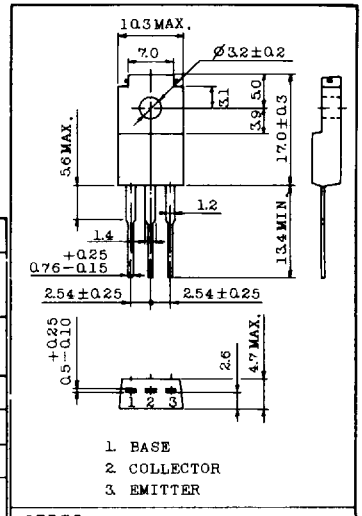
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

. High Transition Frequency : f_T=100MHz (Typ.)

. Complementary to 2SA1306B

Unit in mm



JEDEC	–
EIAJ	–
TOSHIBA	2-10L1A

Weight : 2.1g

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	2SC3298B	V_{CBO}	200	V
Collector-Emitter Voltage	2SC3298B	V_{CEO}	200	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	1.5	A
Base Current		I_B	0.15	A
Collector Power Dissipation (Tc=25°C)		P_C	20	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55 ~ 150	°C

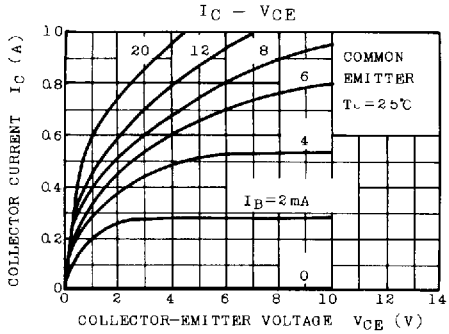
www.DataSheet4U.com

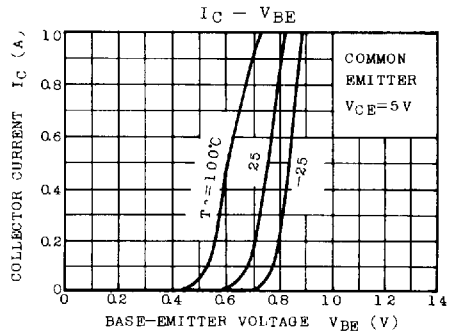
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=160V, I_E=0	–	–	1.0	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=5V, I_C=0	–	–	1.0	μA
Collector-Emitter Breakdown Voltage	2SC3298B	$V_{(BR)CEO}$	I_C=10mA, I_B=0	200	–	–	V
DC Current Gain		h_{FE} (Note)	V_{CE}=5V, I_C=100mA	70	–	240	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=500mA, I_B=50mA	–	–	1.5	V
Base-Emitter Voltage		V_{BE}	V_{CE}=5V, I_C=500mA	–	–	1.0	V
Transition Frequency		f_T	V_{CE}=10V, I_C=100mA	–	100	–	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=10V, I_C=0, f=1MHz	–	25	–	pF

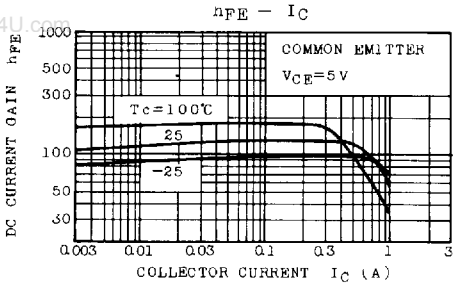
Note : h_{FE} Classification O : 70 ~ 140, Y : 120 ~ 240

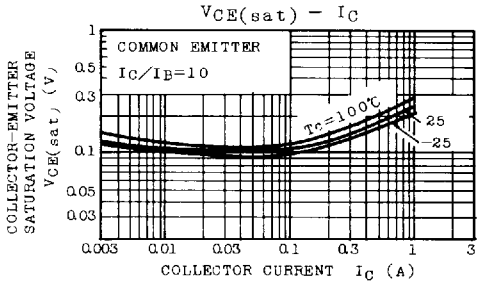
www.DataSheet4U.com

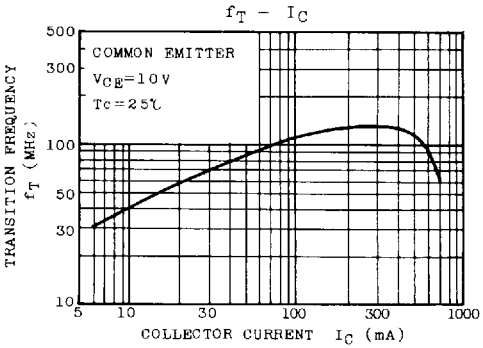


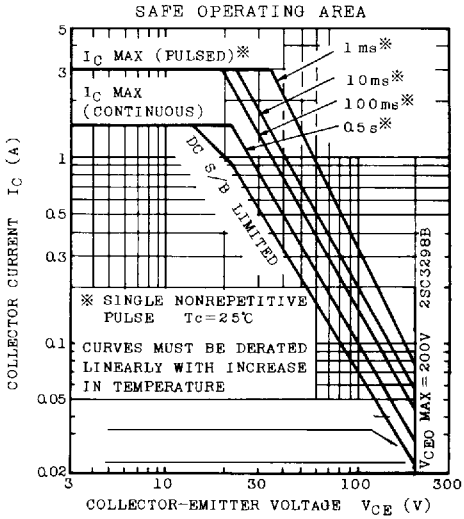


www.DataSheet4U.com









www.DataSheet4U.com